

[METHOD OF FABRICATING SHALLOW TRENCH ISOLATION STRUCTURE FOR REDUCING WAFER SCRATCH]

Abstract

A method of fabricating a shallow trench isolation structure for reducing wafer scratchreducing scratch on a wafer surface is provided. A parameter of a processing operation is controlled in a manner to reduce an amassment of material over the wafer surface. Thus, a step height from the surface of the substrate, which would otherwise cause micro-scratches on the wafer surface in a subsequent chemical-mechanical polishing operation, can be effectively reduced.